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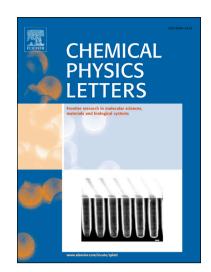
PII: S0009-2614(17)31089-8

DOI: https://doi.org/10.1016/j.cplett.2017.12.010

Reference: CPLETT 35286

To appear in: Chemical Physics Letters

Received Date: 12 August 2017 Accepted Date: 5 December 2017



Please cite this article as: H. Li, S. Huang, Q. Zhang, Z. Zhu, C. Li, J. Meng, Y. Tian, Nonmetal doping induced electronic and magnetic properties in MoSe₂ monolayer, *Chemical Physics Letters* (2017), doi: https://doi.org/10.1016/j.cplett.2017.12.010

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Nonmetal doping induced electronic and magnetic properties in

MoSe₂ monolayer

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Abstract

We have systematically investigated the electronic structures and magnetic properties of nonmetal doped MoSe₂ monolayer by using spin-polarized density functional theory calculations. Formation energies reveal that all doped systems are thermodynamically preferred under Mo-rich conditions than Se-rich conditions, and the incorporation of O atom into MoSe₂ monolayer is most favorable. Electronic structure analysis elucidates that Cl, Br and I doped systems exhibit half-metallic properties, while the band gap has been significantly tuned by H, B, C, N, and F doping. More importantly, H, B, N, F, Cl, Br, and I doping can induce pronounced magnetic moments in host MoSe₂ monolayer.

Keywords: density functional theory; MoSe₂ monolayer; nonmetals doping; electronic and magnetic properties

1. Introduction

Transition metal dichalcogenides (TMDs), belong to the family of layered materials, attract great scientific and technological interest due to their potential

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